

# Virginie Hoel

## List of Publications by Year in descending order

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21  
papers

373  
citations

1039406

9  
h-index

1058022

14  
g-index

21  
all docs

21  
docs citations

21  
times ranked

480  
citing authors

#	ARTICLE	IF	CITATIONS
1	A 4-fj/Spike Artificial Neuron in 65 nm CMOS Technology. <i>Frontiers in Neuroscience</i> , 2017, 11, 123.	1.4	126
2	Power Performance at 40 GHz of AlGaIn/GaN High-Electron Mobility Transistors Grown by Molecular Beam Epitaxy on Si(111) Substrate. <i>IEEE Electron Device Letters</i> , 2015, 36, 303-305.	2.2	55
3	Effect of the T-gate on the performance of recessed HEMTs. A Monte Carlo analysis. <i>Semiconductor Science and Technology</i> , 1999, 14, 864-870.	1.0	50
4	Power Performance at 40 GHz on Quaternary Barrier InAlGaIn/GaN HEMT. <i>IEEE Electron Device Letters</i> , 2013, 34, 978-980.	2.2	36
5	Optimization of $\{m Al\}_{0.29}\{m Ga\}_{0.71}\{m N\}/\{m GaN\}$ High Electron Mobility Heterostructures for High-Power/Frequency Performances. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 3105-3111.	1.6	22
6	Recent improvements of flexible GaN-based HEMT technology. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600484.	0.8	18
7	A converging route towards very high frequency, mechanically flexible, and performance stable integrated electronics. <i>Journal of Applied Physics</i> , 2013, 113, 153701.	1.1	16
8	AlGaIn/GaN HEMTs on a (001)-Oriented Silicon Substrate Based on 100-nm SiN Recessed Gate Technology for Microwave Power Amplification. <i>IEEE Transactions on Electron Devices</i> , 2007, 54, 2843-2848.	1.6	13
9	AlGaIn/GaN HEMT High Power Densities on $\text{SiC}/\text{SiO}_2/\text{poly-SiC}$ Substrates. <i>IEEE Electron Device Letters</i> , 2009, 30, 596-598.	2.2	11
10	Thermal behavior analysis of GaN based epi material on different substrates by means of a physical thermal model. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010, 207, 1820-1826.	0.8	7
11	Impact of the Bending on the Electroluminescence of Flexible InGaIn/GaN Light-Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , 2016, 28, 1661-1664.	1.3	6
12	Temperature and Gate-Length Dependence of Subthreshold RF Detection in GaN HEMTs. <i>Sensors</i> , 2022, 22, 1515.	2.1	5
13	Stochastic model for action potential simulation including ion shot noise. <i>Journal of Computational Electronics</i> , 2017, 16, 419-430.	1.3	4
14	Monte Carlo simulation of electronic characteristics in short channel $\hat{\Gamma}$ -doped AlInAs/GaInAs HEMTs. <i>Microelectronics Reliability</i> , 2001, 41, 73-77.	0.9	2
15	Low-frequency noise behavior in GaN HEMTs on silicon substrate. , 2004, , .		2
16	<title>94-GHz MMIC CPW low-noise amplifier on InP</title>. , 1999, , .		0
17	Recent Achievement in the GaN Epitaxy on Silicon and Engineering Substrates. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1108, 1.	0.1	0
18	Emphasis on trap activity in AlGaIn/GaN HEMTs through temperature dependent pulsed I-V characteristics. <i>EPJ Applied Physics</i> , 2013, 64, 20101.	0.3	0

#	ARTICLE	IF	CITATIONS
19	Polarization Engineering of Al(Ga)N/GaN HEMT Structures for Microwave High Power Applications. Materials Science Forum, 0, 806, 81-87.	0.3	0
20	Characterization and modeling of traps and RF frequency dispersion in AlGaIn/AlN/GaN HEMTs. , 2016, , .		0
21	Experimental investigation of stochastic resonance in a 65nm CMOS artificial neuron. , 2017, , .		0